

Description:

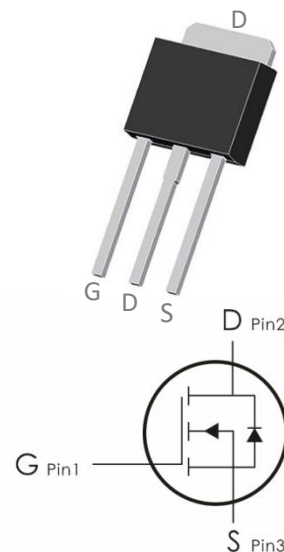
This N-Channel MOSFET uses advanced trench technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=100A, R_{DS(ON)}<4m\Omega @V_{GS}=10V$ (Typ: $3.3m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
UC004NG-B	C004N-B	TO- 251	80 pcs/Tube

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹	100	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$ ¹	70	
I_{DM}	Pulsed Drain Current ²	400	
P_D	Power Dissipation	74	W
E_{AS}	Single pulse avalanche energy ³	110	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.7	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =30V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1	1.6	3	V
R _{DS(ON)}	Drain-Source On Resistance ⁴	V _{GS} =10V, I _D =20A	---	3.3	4	m Ω
		V _{GS} =4.5V, I _D =10A	---	5	6	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2300	---	pF
C _{oss}	Output Capacitance		---	289	--	
C _{rss}	Reverse Transfer Capacitance		---	243	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =15V, I _D =30A, R _{ENG} =3 Ω ,V _{GS} =10V	---	9	---	ns
t _r	Rise Time		---	15	---	ns
t _{d(off)}	Turn-Off Delay Time		---	37.8	---	ns
t _f	Fall Time		---	11	---	ns
Q _{gs}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =30A	---	42	---	nC
Q _{gd}	Gate-Source Charge		---	9	---	nC
Q _g	Gate-Drain “Miller” Charge		---	10.5	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =30A	---	---	1.2	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	83.3	A
I _{SM}	Pulsed Drain Current		---	---	333.3	A
T _{rr}	Reverse Recovery Time	I _F =20A, T _J =25 °C	---	11	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/us	---	2.5	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C$, $V_{DD}=15V$, $V_G=10V$, $L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Characteristics: ($T_c=25^{\circ}C$ unless otherwise noted)

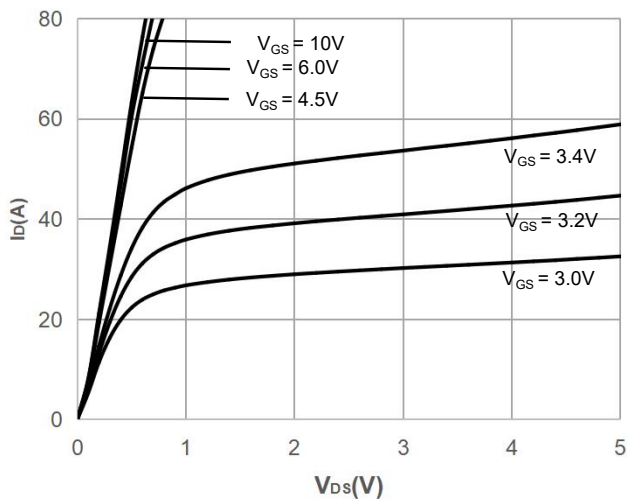


Figure 1: Output Characteristics

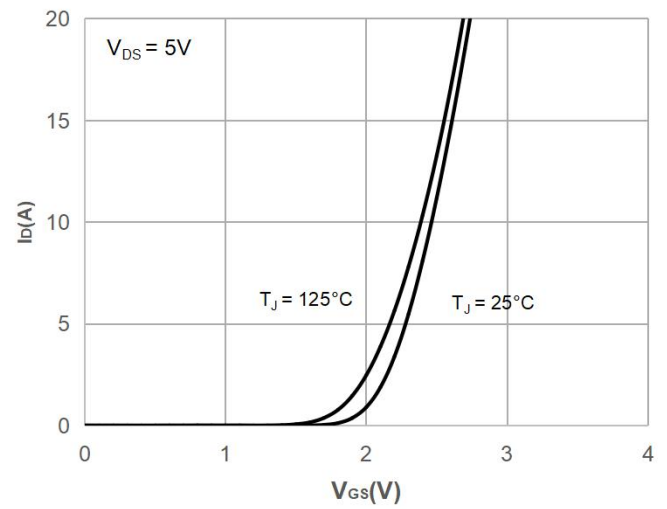


Figure 2: Typical Transfer Characteristics

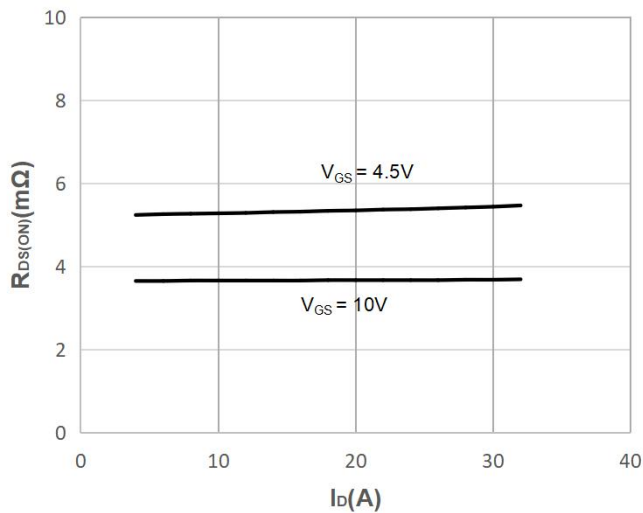


Figure 3: On-resistance vs. Drain Current

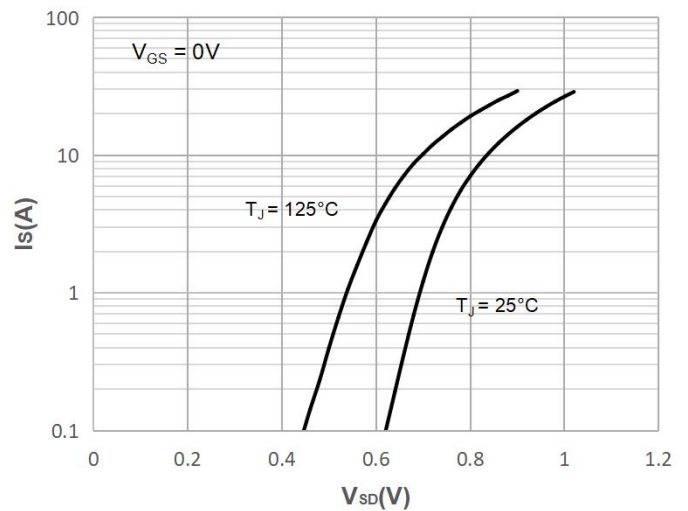


Figure 4: Body Diode Characteristics

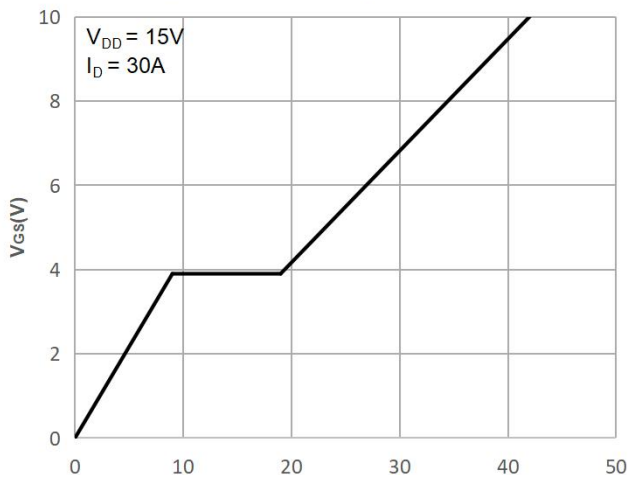


Figure 5: Gate Charge Characteristics

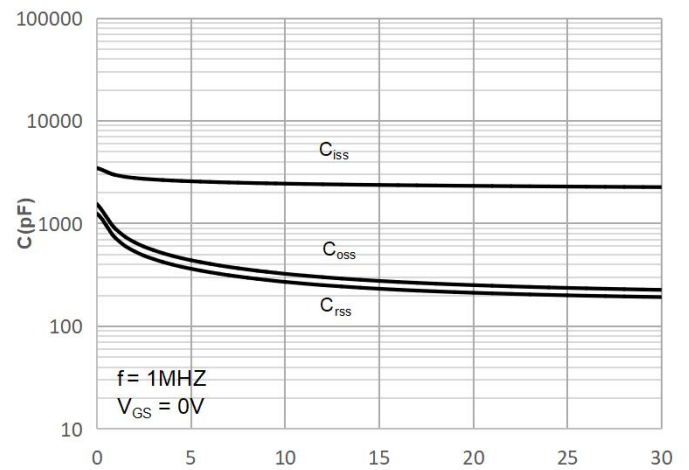


Figure 6: Capacitance Characteristics

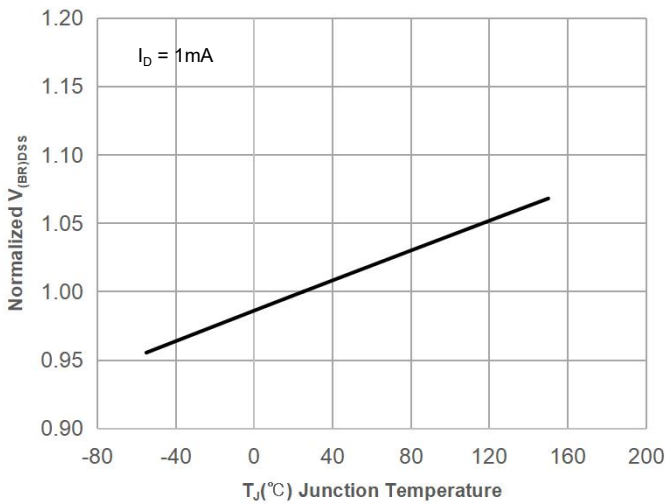


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

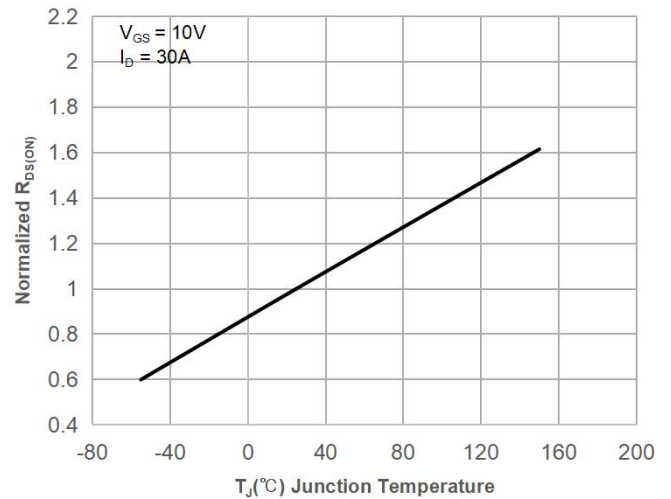


Figure 8: Normalized on Resistance vs. Junction Temperature

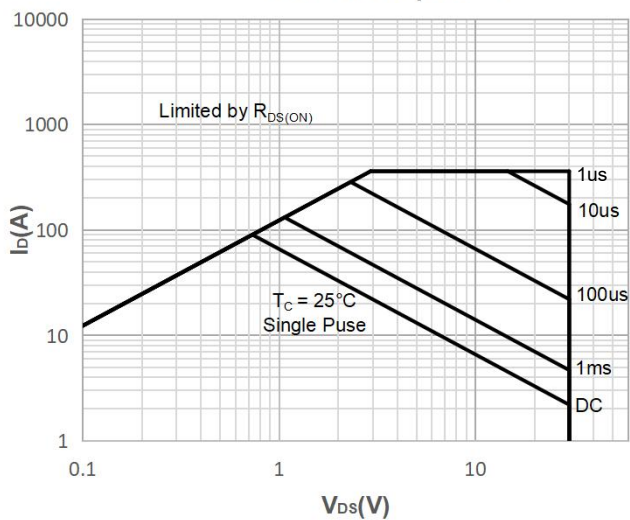


Figure 9: Maximum Safe Operating Area

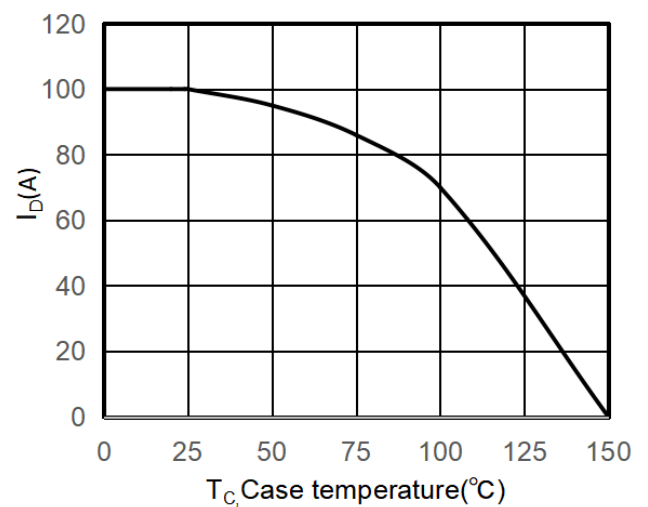


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

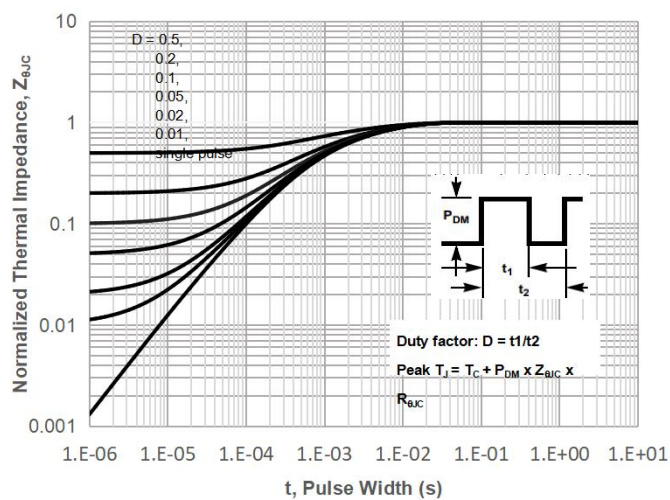


Figure 11: Normalized Maximum Transient Thermal Impedance

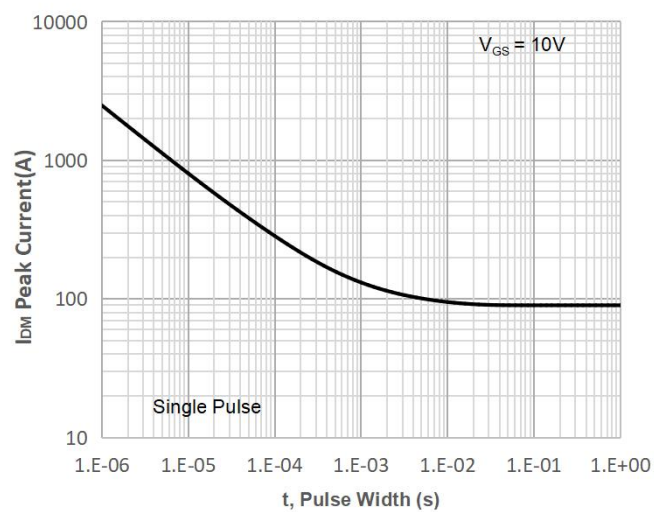
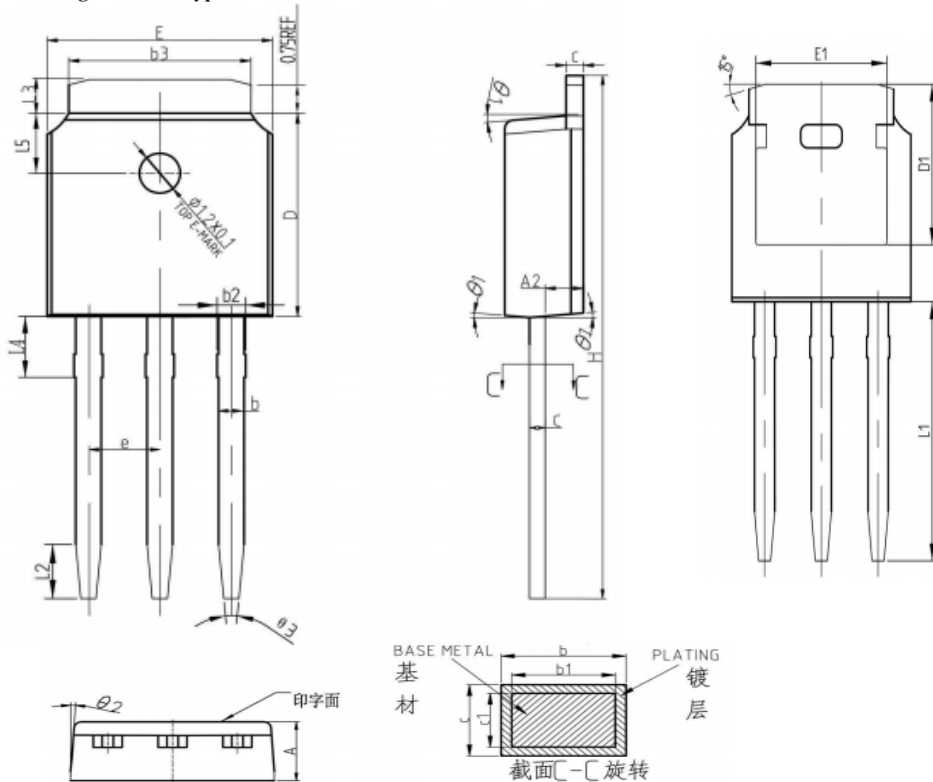


Figure 12: Peak Current Capacity

TO-251 Package Information

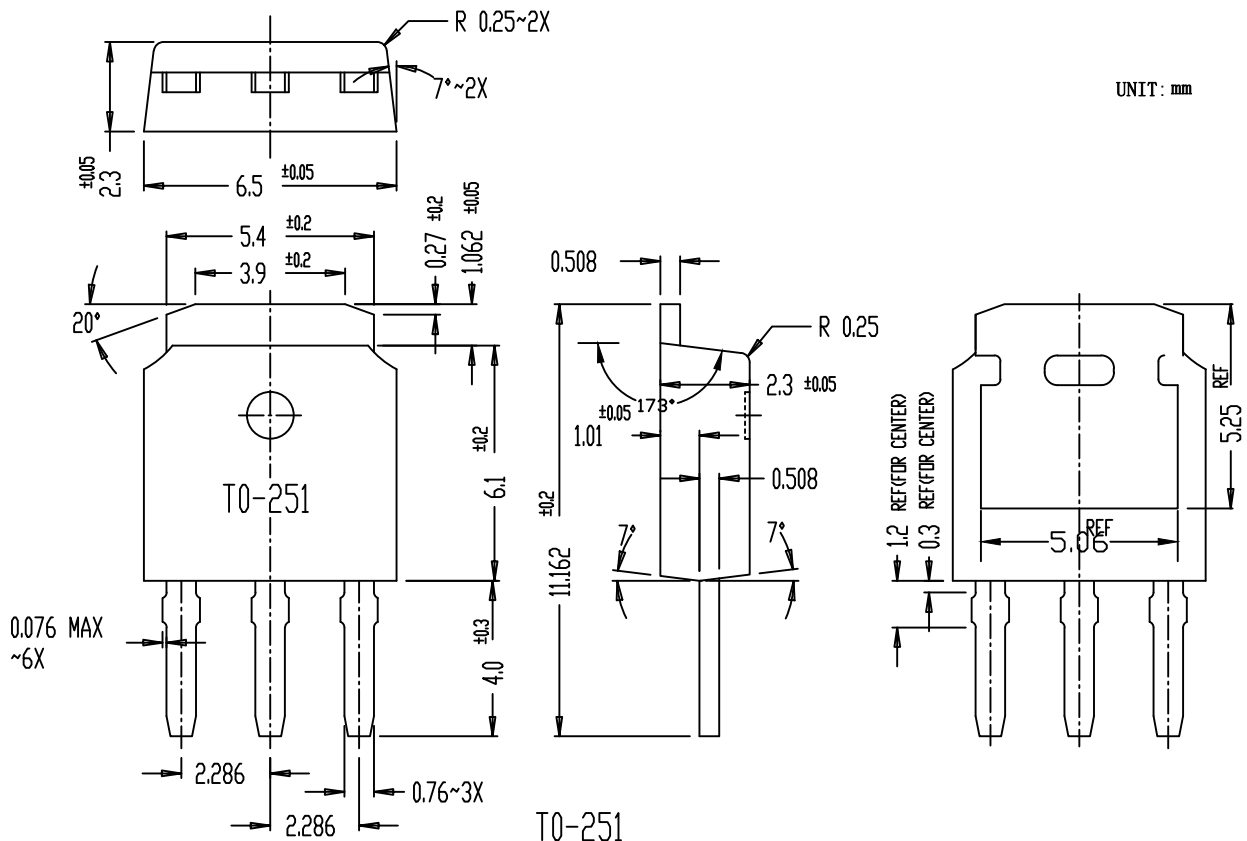
Package Outline Type-A



SYMBOL	mm		
	MIN	NOM	MAX
*A	2.20	2.30	2.38
*A2	0.97	1.07	1.17
*b	0.72	0.78	0.85
b1	0.71	0.76	0.81
*b2	0.72	0.88	0.95
*b3	5.23	5.33	5.46
*c	0.47	0.53	0.58
c1	0.46	0.51	0.56
*D	6.00	6.10	6.20
D1	5.30REF		
*E	6.50	6.60	6.70
E1	4.70	4.83	4.92
*e	2.286BSC		
*H	16.10	16.40	16.60
*L1	9.20	9.40	9.60
L2	1.25	1.35	1.45
*L3	0.90	1.02	1.22
L4	0.95	1.05	1.15
L5	1.70	1.80	1.90
θ 1	5°	7°	9°
θ 2	5°	7°	9°
θ 3	11°	13°	15°

带*为检验尺寸

Package Outline Type-B



T0-251

Marking Information:

①. Doingter LOGO

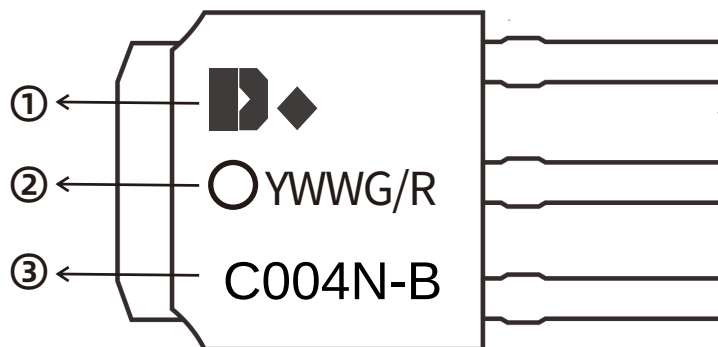
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



Previous Version

Version	Date	Subjects (major changes since last revision)
2.0	2025-11-08	Release of final version

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